1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in a robust LFPAK56 package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
 - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
 - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
 - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - · Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
 - · Improved reliability, with reduced Rth and RDSon
 - · Increases maximum current capability and improved current spreading

3. Applications

- 12 V automotive systems
- · Motors, lamps and solenoid control
- · Start-Stop micro-hybrid applications
- · Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	163	W



N-channel 40 V, 2.4 m Ω logic level MOSFET in LFPAK56

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static characte	eristics					,
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 25 °C; Fig. 10	1.35	1.93	2.4	mΩ
Dynamic chara	acteristics					
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	-	5.9	11.7	nC
Source-drain o	liode					
Q _r	recovered charge	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	24.9	-	nC
S	softness factor	V _{DS} = 20 V	-	0.85	-	

^{[1] 120}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G (F)
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package	ackage				
	Name	Description	Version			
BUK9Y2R4-40H	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669			

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9Y2R4-40H	92H440

8. Limiting values

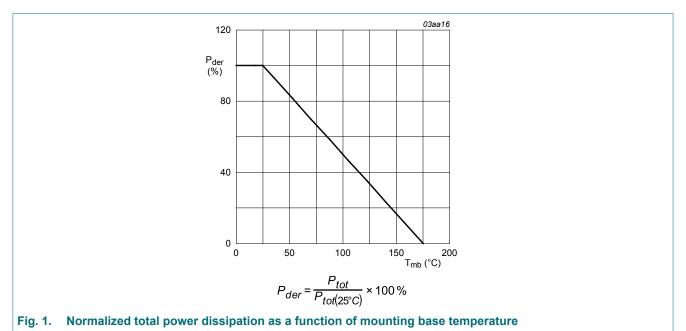
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V _{GS}	gate-source voltage	DC; T _j ≤ 175 °C		-10	16	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	163	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C	[1]	-	120	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 2		-	600	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
Is	source current	T _{mb} = 25 °C		-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	600	Α
Avalanche r	uggedness			'		
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 120 A; $V_{sup} \le$ 40 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; Fig. 3; unclamped	[2] [3]	-	81.5	mJ

^{[1] 120}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature

^[3] Refer to application note AN10273 for further information.



^[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

N-channel 40 V, 2.4 m Ω logic level MOSFET in LFPAK56

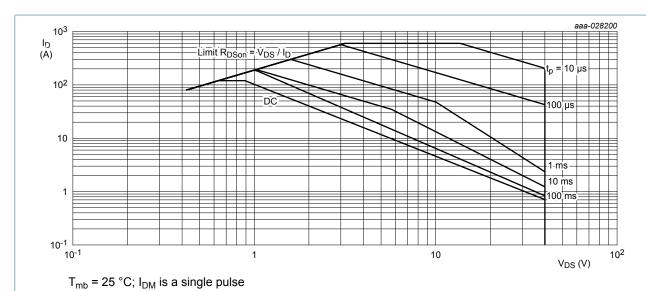


Fig. 2. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

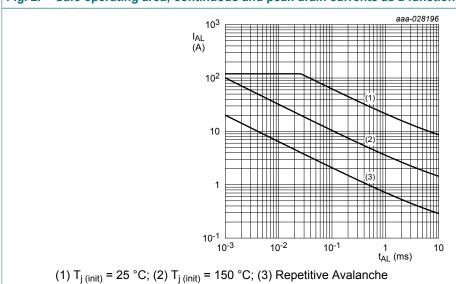


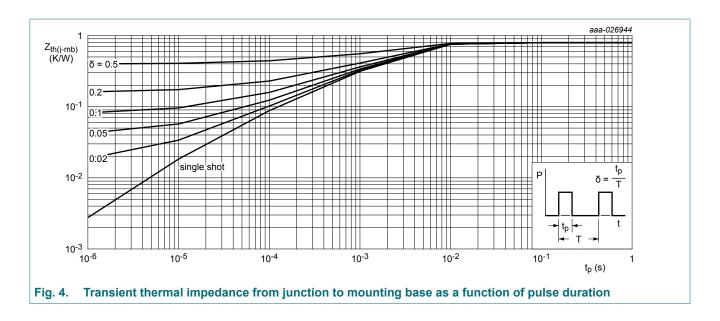
Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.63	0.79	K/W

N-channel 40 V, 2.4 m Ω logic level MOSFET in LFPAK56



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	43	-	V V V V V V μA μA μA
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -40 ^{\circ}C$	-	40.5	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 8; Fig. 9$	1.35	1.66	2.05	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 °C; Fig. 9$	0.6	-	-	V V V V V V μA μA μA
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$	-	-	2.5	
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.06	5	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	1.2	10	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	142	500	μΑ
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	1.35	1.93	2.4	Unit mΩ mΩ mΩ mΩ mΩ mΩ mΩ m
		V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; Fig. 11	2	2.95	3.8	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 11	2.2	3.2	4.2	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11	2.8	4.11	5.2	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; Fig. 10	1.68	2.4 3.2 3.67 5 4 5.7 5.11 7 0.72 1.8 55.8 78.2 25.3 35.4 9.9 14.9 5.9 11.7 3960 5544	mΩ	
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 105 °C; Fig. 11	2.5	3.67	5	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 125 °C; Fig. 11	2.8	4	5.7	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 175 °C; Fig. 11	3.5	5.11	7	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.29	0.72	1.8	Ω
Dynamic cl	haracteristics		'			
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 20 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	55.8	78.2	nC
		I _D = 25 A; V _{DS} = 20 V; V _{GS} = 4.5 V;	-	25.3	35.4	nC
Q _{GS}	gate-source charge	Fig. 12; Fig. 13	-	9.9	14.9	nC
Q _{GD}	gate-drain charge		-	5.9	11.7	nC
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	3960	5544	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	859	1203	pF
C _{rss}	reverse transfer capacitance		-	140	308	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 20 \text{ V}; R_L = 0.8 \Omega; V_{GS} = 4.5 \text{ V};$	-	23.1	-	ns
t _r	rise time	g. 12; Fig. 13 DS = 25 V; V _{GS} = 0 V; f = 1 MHz; = 25 °C; Fig. 14 DS = 20 V; R _L = 0.8 Ω; V _{GS} = 4.5 V;	-	26.3	-	ns
t _{d(off)}	turn-off delay time		-	27.2	-	ns
t _f	fall time	1	-	16.4	-	ns
Source-dra	in diode					
V _{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _i = 25 °C; <u>Fig. 15</u>	-	0.8	1.2	V
t _{rr}	reverse recovery time	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ $v_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ $v_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 105 \text{ °C};$ $v_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 105 \text{ °C};$ $v_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 125 \text{ °C};$ $v_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ $v_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V}; I_D = 175 \text{ °C};$ $v_{GS} = 10 \text{ V};$ v_{GS}	-	31	-	ns
Q _r	recovered charge		-	24.9	-	nC
S	softness factor		-	0.85	-	
		I _S = 25 A; dI _S /dt = -500 A/μs; V _{GS} = 0 V; V _{DS} = 20 V	-	0.67	-	

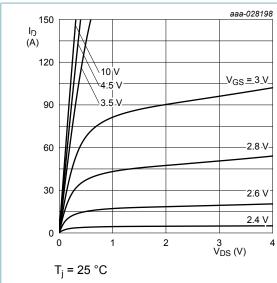


Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values

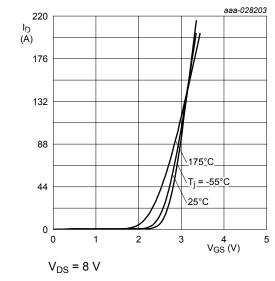


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

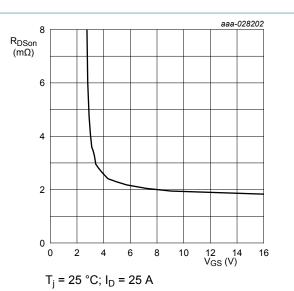


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

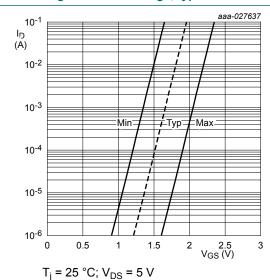


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

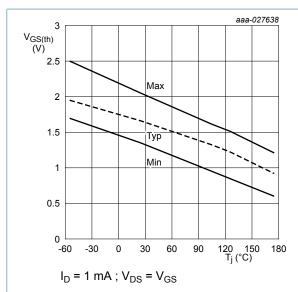


Fig. 9. Gate-source threshold voltage as a function of junction temperature

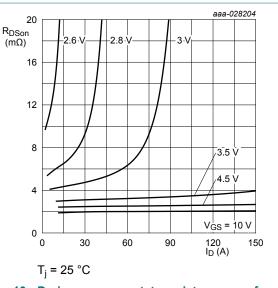


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

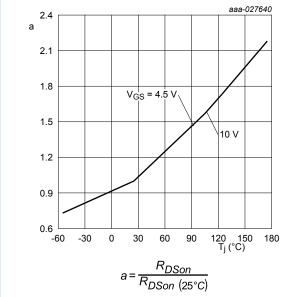


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

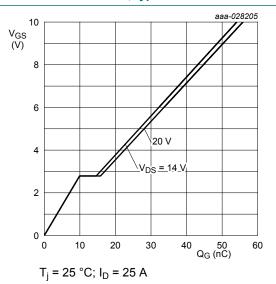


Fig. 12. Gate-source voltage as a function of gate charge; typical values

N-channel 40 V, 2.4 m Ω logic level MOSFET in LFPAK56

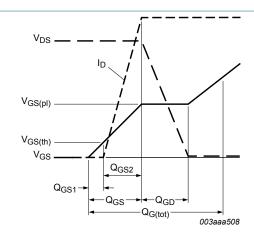
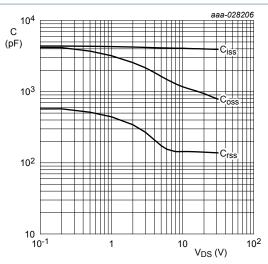


Fig. 13. Gate charge waveform definitions

 $V_{GS} = 0 V$



 $V_{GS} = 0 V$; f = 1 MHz

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

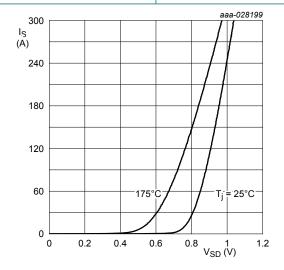
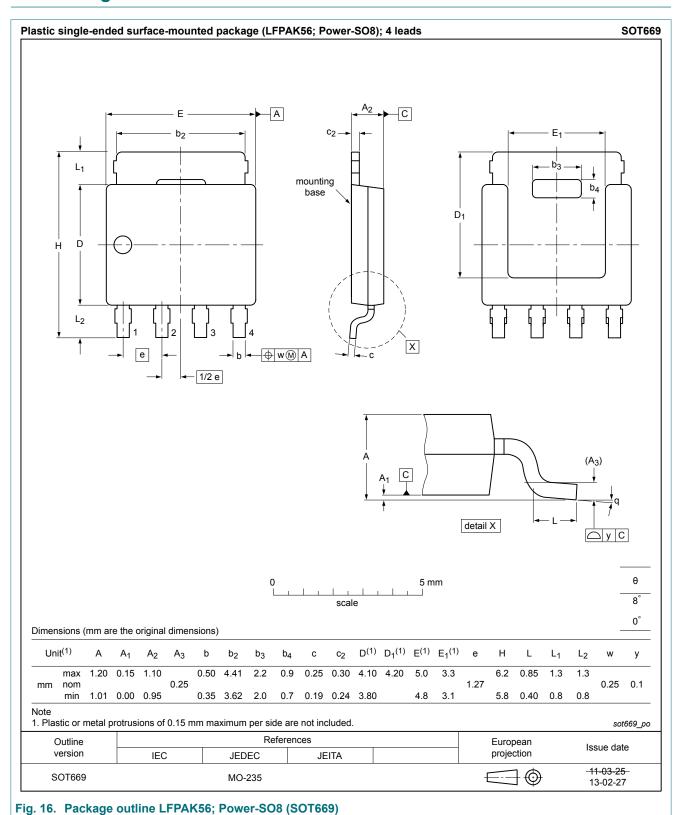


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

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11. Package outline



N-channel 40 V, 2.4 mΩ logic level MOSFET in LFPAK56

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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BUK9Y2R4-40H

N-channel 40 V, 2.4 m Ω logic level MOSFET in LFPAK56

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